

ZXTP25140BFH

140V, SOT23, PNP medium power transistor

Summary

$BV_{(BR)CEX} > -180V$; $BV_{(BR)CEO} > -140V$

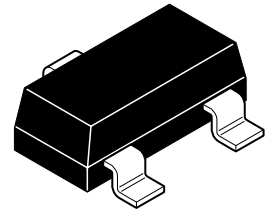
$BV_{(BR)ECO} > -7V$;

$I_{C(cont)} = -1A$

$R_{ce(sat)} = 180\text{ m}\Omega$ typical

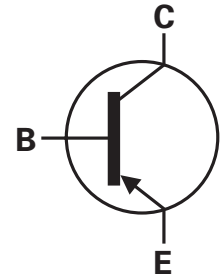
$V_{ce(sat)} < -260\text{mV @ } 1A$;

$P_D = 1.25W$



Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.



Features

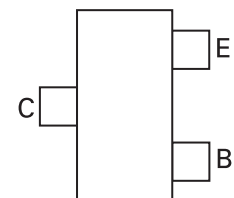
- High power dissipation SOT23 package
- 180V forward blocking voltage
- Low saturation voltage

Applications

- DC-DC converters
- High side switching

Ordering information

Device	Reel size (inches)	Tape width	Quantity per reel
ZXTP25140BFHTA	7	8mm	3,000



Pinout - top view

Device marking

026

ZXTP25140BFH

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V_{CBO}	-180	V
Collector-emitter voltage (forward blocking)	V_{CEX}	-180	V
Collector-emitter voltage	V_{CEO}	-140	V
Emitter-collector voltage (reverse blocking)	V_{ECO}	-7	V
Emitter-base voltage	V_{EBO}	-7	V
Continuous collector current ^(a)	I_C	-1	A
Peak pulse current	I_{CM}	-3	A
Power dissipation at $T_A=25^\circ\text{C}$ ^(a) Linear derating factor	P_D	0.73 5.84	W mW/°C
Power dissipation at $T_A=25^\circ\text{C}$ ^(b) Linear derating factor	P_D	1.05 8.4	W mW/°C
Power dissipation at $T_A=25^\circ\text{C}$ ^(c) Linear derating factor	P_D	1.25 9.6	W mW/°C
Power dissipation at $T_A=25^\circ\text{C}$ ^(d) Linear derating factor	P_D	1.81 14.5	W mW/°C
Operating and storage temperature range	T_j, T_{stg}	-55 to 150	°C

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	171	°C/W
Junction to ambient ^(b)	$R_{\theta JA}$	119	°C/W
Junction to ambient ^(c)	$R_{\theta JA}$	100	°C/W
Junction to ambient ^(d)	$R_{\theta JA}$	69	°C/W

NOTES:

(a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

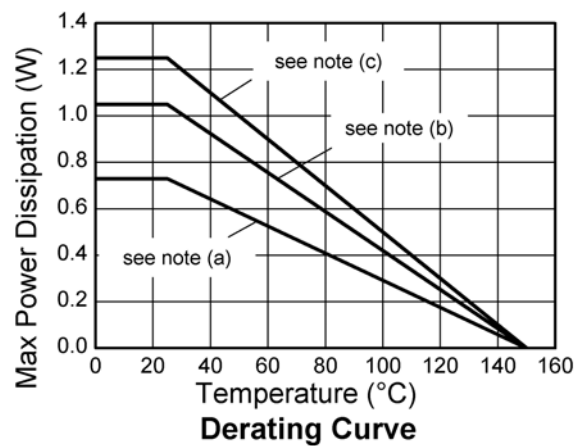
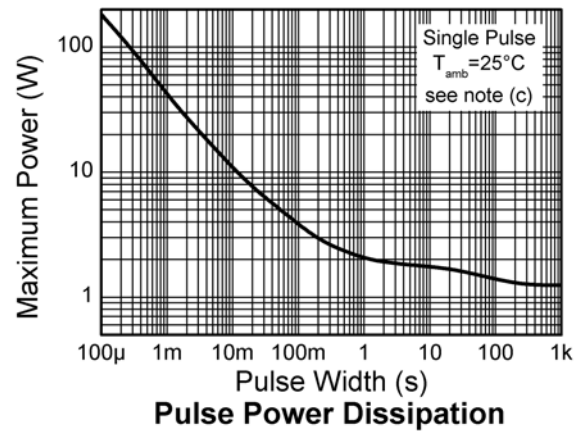
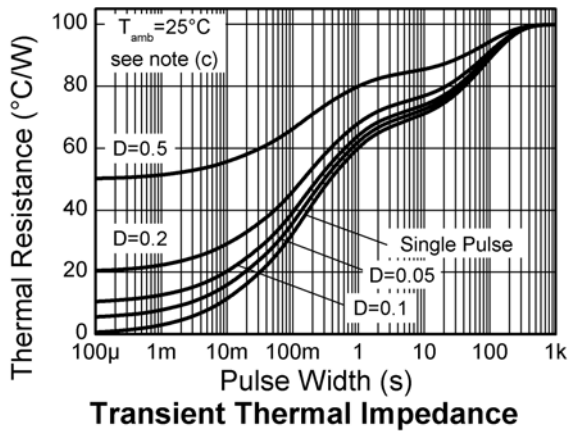
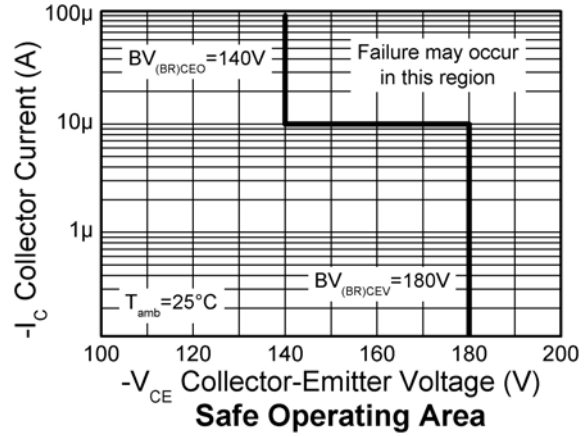
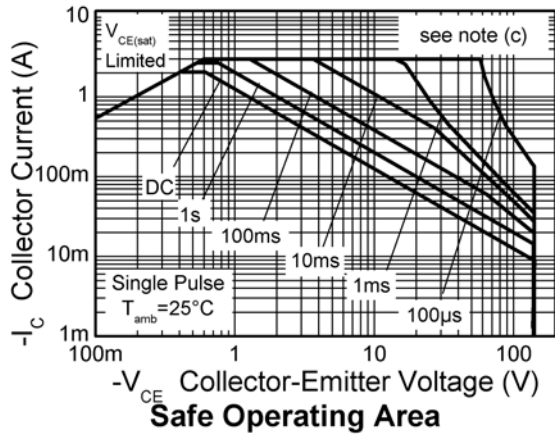
(b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(d) As (c) above measured at $t < 5$ secs.

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Characteristics



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Electrical characteristics (at $T_{AMB} = 25^{\circ}\text{C}$ unless otherwise stated)

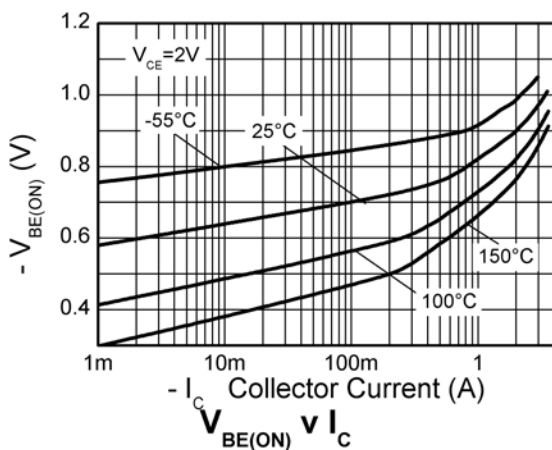
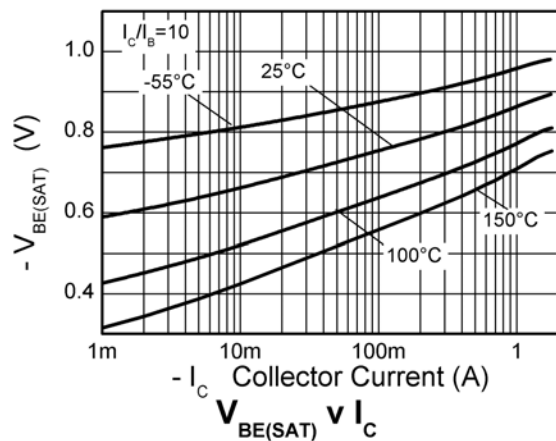
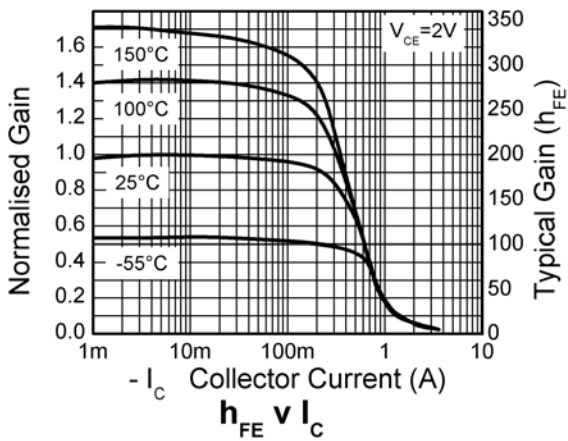
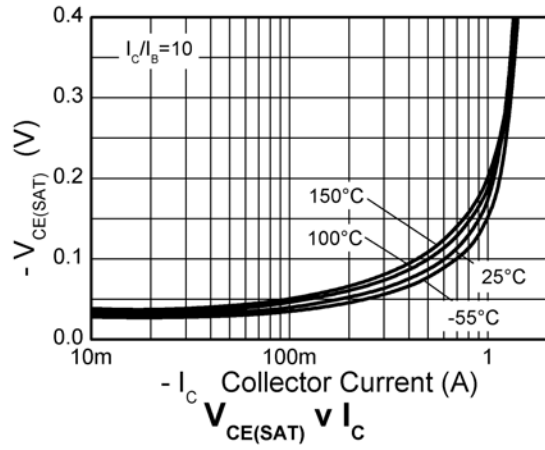
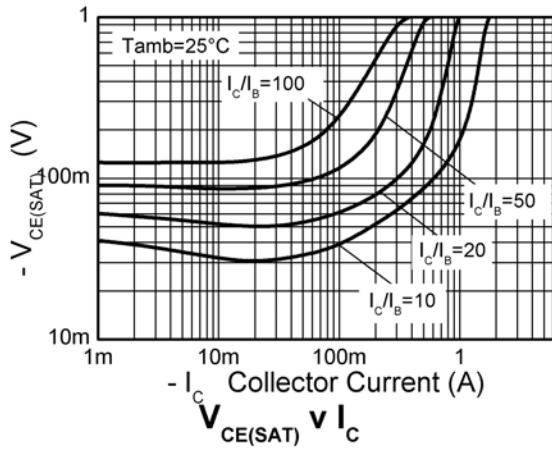
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	-180	-205		V	$I_C = -100\mu\text{A}$
Collector-emitter breakdown voltage (forward blocking)	BV_{CEX}	-180	-205		V	$I_C = -100\mu\text{A}$, $R_{BE} \leq 1\text{k}\Omega$ or $-0.25\text{V} < V_{BE} < 1\text{V}$
Collector-emitter breakdown voltage (base open)	BV_{CEO}	-140	-160		V	$I_C = -10\text{mA}$ (*)
Emitter-collector breakdown voltage (reverse blocking)	BV_{ECO}	-7	-8.5		V	$I_E = -100\mu\text{A}$ (*)
Emitter-base breakdown voltage	BV_{EBO}	-7	-8.2		V	$I_E = -100\mu\text{A}$
Collector cut-off current	I_{CBO}		<-1	-50 -20	nA μA	$V_{CB} = -144\text{V}$ $V_{CB} = -144\text{V}$, $T_{AMB} = 100^{\circ}\text{C}$
Collector emitter cut-off current	I_{CEX}		-	-100	nA	$V_{CE} = -144\text{V}$; $R_{BE} \leq 1\text{k}\Omega$ or $-0.25\text{V} < V_{BE} < 1\text{V}$
Emitter cut-off current	I_{EBO}		<-1	-50	nA	$V_{EB} = -5.6\text{V}$
Collector-emitter saturation voltage	$V_{ce(sat)}$		-40	-50	mV	$I_C = -0.1\text{A}$, $I_B = -10\text{mA}$ (*)
			-110	-135	mV	$I_C = -0.1\text{A}$, $I_B = -2\text{mA}$ (*)
			-90	-110	mV	$I_C = -0.5\text{A}$, $I_B = -50\text{mA}$ (*)
			-170	-230	mV	$I_C = -0.5\text{A}$, $I_B = -25\text{mA}$ (*)
			-180	-260	mV	$I_C = -1\text{A}$, $I_B = -100\text{mA}$ (*)
Base-emitter saturation voltage	$V_{be(sat)}$		-850	-950	mV	$I_C = -1\text{A}$, $I_B = -100\text{mA}$ (*)
Base-emitter turn-on voltage	$V_{BE(ON)}$		-800	-900	mV	$I_C = -1\text{A}$, $V_{CE} = -2\text{V}$ (*)
Static forward current transfer ratio	h_{FE}	100	200	300		$I_C = -10\text{mA}$, $V_{CE} = -2\text{V}$ (*)
		100	190			$I_C = -0.1\text{A}$, $V_{CE} = -2\text{V}$ (*)
		20	30			$I_C = -1\text{A}$, $V_{CE} = -2\text{V}$ (*)
Transition frequency	f_T		75		MHz	$I_C = -10\text{mA}$, $V_{CE} = -20\text{V}$ $f = 20\text{MHz}$
Output capacitance	C_{OBO}		10		pF	$V_{CB} = -20\text{V}$, $f = 1\text{MHz}$ (*)
Turn-on time	$t_{(on)}$		102		ns	$V_{CC} = -20\text{V}$, $I_C = -100\text{mA}$, $I_{B1} = I_{B2} = -10\text{mA}$
Turn-off time	$t_{(off)}$		854		ns	

NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

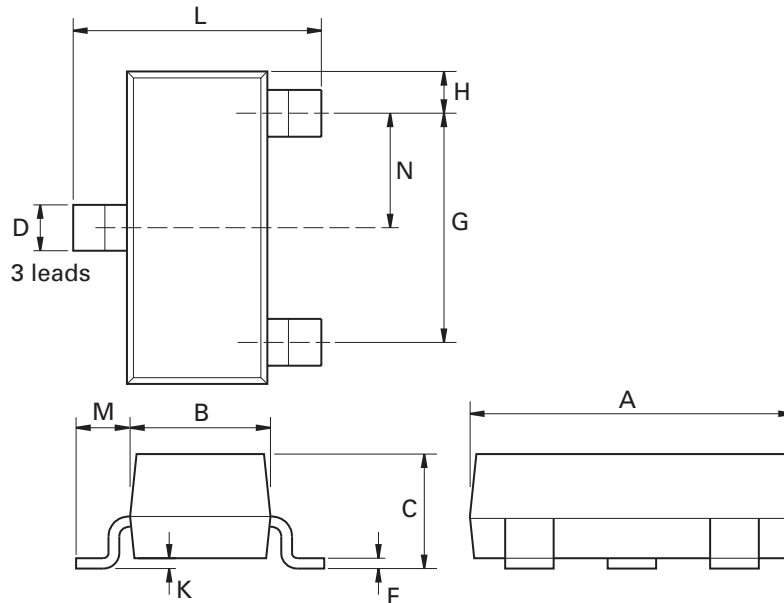
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Typical characteristics



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Package outline - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	-	1.10	-	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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